Abstracts

Performances of Laser-Processed HEMTs with AIAs-nGaAs Superlattice Donor Layers

J.M. Dumas, A. Christou, A. Belhadj, G. Kiriakidis, Z. Hatzopoulos, P. Audren, H. Thomas and J. Goostray. "Performances of Laser-Processed HEMTs with AIAs-nGaAs Superlattice Donor Layers." 1989 MTT-S International Microwave Symposium Digest 89.1 (1989 Vol. I [MWSYM]): 483-486.

In-site laser resorption of GaAs semi-insulating substrate surfaces prior to MBE growth and laser processing of ohmic contacts have been used for the fabrication of X-band HEMTs with superlattice donor layers. The improvements made lead to high performance devices.

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